

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

Claims 1-7 (cancelled)

8. (Currently amended) A method for making a field effect transistor with a current channel with longitudinal stress, comprising the steps of:

- a) selectively forming an undercut area under the channel in selected regions of the perimeter of said channel; and
- b) forming a compressive film in the undercut area so that longitudinal stress is created in the channel.

9. (Currently amended) The method of claim 8 wherein the undercut area is selectively located under at least one at an end of the channel.

10. (Currently amended) The method of claim 8 wherein the undercut is selectively located under a middle portion of the channel.

11. (Original) The method of claim 10 wherein the channel is released in the middle portion.

12. (Original) The method of claim 8 wherein the undercut area is created by etching a buried oxide layer from under the channel.

13. (Original) The method of claim 8 wherein the compressive film is formed by depositing polysilicon and then oxidizing the polysilicon.

Claims 14-15 (cancelled)

16. (New) The method of claim 8 wherein two regions of said channel perimeter are selected for undercut formation.